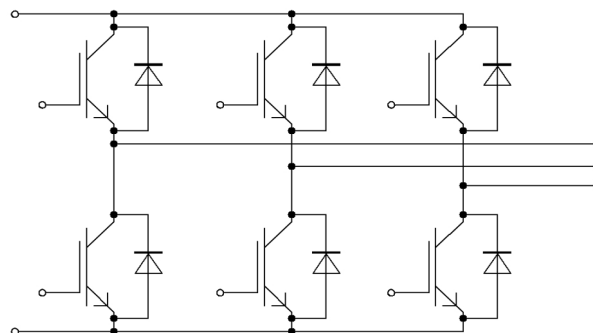
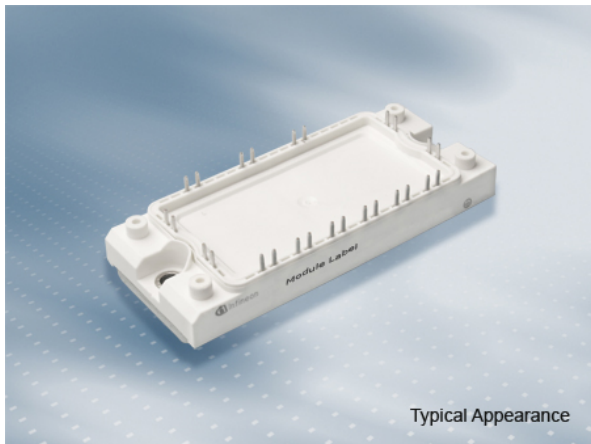




EconoPACK™2 Modul mit Trench/Feldstopp IGBT3 und Emitter Controlled 3 Diode  
EconoPACK™2 module with Trench/Fieldstop IGBT3 and Emitter Controlled 3 diode



$V_{CES} = 1700V$   
 $I_{C\ nom} = 50A / I_{CRM} = 100A$

**Typische Anwendungen**

- Hilfsumrichter
- Motorantriebe

**Elektrische Eigenschaften**

- Hohe Kurzschlussrobustheit, selbstlimitierender Kurzschlussstrom
- Niedrige Schaltverluste
- $V_{CESat}$  mit positivem Temperaturkoeffizienten
- Niedriges  $V_{CESat}$

**Mechanische Eigenschaften**

- Kupferbodenplatte
- Standardgehäuse

**Typical Applications**

- Auxiliary Inverters
- Motor Drives

**Electrical Features**

- High Short Circuit Capability, Self Limiting Short Circuit Current
- Low Switching Losses
- $V_{CESat}$  with positive Temperature Coefficient
- Low  $V_{CESat}$

**Mechanical Features**

- Copper Base Plate
- Standard Housing

**Module Label Code**

Barcode Code 128



DMX - Code



**Content of the Code**

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

prepared by: RH	date of publication: 2013-10-03	
approved by: RS	revision: 3.0	UL approved (E83335)



**IGBT, Wechselrichter / IGBT, Inverter**

**Höchstzulässige Werte / Maximum Rated Values**

Kollektor-Emitter-Sperrspannung Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	1700	V
Kollektor-Dauergleichstrom Continuous DC collector current	$T_C = 80^{\circ}\text{C}, T_{vj\text{max}} = 150^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 150^{\circ}\text{C}$	$I_{C\text{nom}}$ $I_C$	50 82	A A
Periodischer Kollektor-Spitzenstrom Repetitive peak collector current	$t_P = 1\text{ ms}$	$I_{CRM}$	100	A
Gesamt-Verlustleistung Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\text{max}} = 150$	$P_{tot}$	345	W
Gate-Emitter-Spitzenspannung Gate-emitter peak voltage		$V_{GES}$	+/-20	V

**Charakteristische Werte / Characteristic Values**

			min.	typ.	max.	
Kollektor-Emitter-Sättigungsspannung Collector-emitter saturation voltage	$I_C = 50\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 50\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{sat}}$	2,00 2,40	2,45	V V
Gate-Schwellenspannung Gate threshold voltage	$I_C = 2,00\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{Eth}}$	5,2	5,8	6,4 V
Gateladung Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		$Q_G$	0,60		$\mu\text{C}$
Interner Gatewiderstand Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	9,5		$\Omega$
Eingangskapazität Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{ies}$	4,50		nF
Rückwirkungskapazität Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{res}$	0,15		nF
Kollektor-Emitter-Reststrom Collector-emitter cut-off current	$V_{CE} = 1700\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$		1,0	mA
Gate-Emitter-Reststrom Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$		400	nA
Einschaltverzögerungszeit, induktive Last Turn-on delay time, inductive load	$I_C = 50\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 8,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{on}}$	0,37 0,40		$\mu\text{s}$ $\mu\text{s}$
Anstiegszeit, induktive Last Rise time, inductive load	$I_C = 50\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 8,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_r$	0,04 0,05		$\mu\text{s}$ $\mu\text{s}$
Abschaltverzögerungszeit, induktive Last Turn-off delay time, inductive load	$I_C = 50\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 8,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{off}}$	0,65 0,80		$\mu\text{s}$ $\mu\text{s}$
Fallzeit, induktive Last Fall time, inductive load	$I_C = 50\text{ A}, V_{CE} = 900\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 8,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_f$	0,18 0,30		$\mu\text{s}$ $\mu\text{s}$
Einschaltverlustenergie pro Puls Turn-on energy loss per pulse	$I_C = 50\text{ A}, V_{CE} = 900\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 1200\text{ A}/\mu\text{s}$ $R_{Gon} = 8,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{on}$	11,0 16,0		mJ mJ
Abschaltverlustenergie pro Puls Turn-off energy loss per pulse	$I_C = 50\text{ A}, V_{CE} = 900\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 3500\text{ V}/\mu\text{s}$ $R_{Goff} = 8,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{off}$	10,5 15,5		mJ mJ
Kurzschlußverhalten SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 1000\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 125^{\circ}\text{C}$		$I_{SC}$	200		A
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro IGBT / per IGBT		$R_{thJC}$		0,36	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	0,19		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj\text{op}}$	-40	125	$^{\circ}\text{C}$

prepared by: RH	date of publication: 2013-10-03
approved by: RS	revision: 3.0



**Diode, Wechselrichter / Diode, Inverter**

**Höchstzulässige Werte / Maximum Rated Values**

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1700	V
Dauergleichstrom Continuous DC forward current		$I_F$	50	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1 \text{ ms}$	$I_{FRM}$	100	A
Grenzlastintegral $I^2t$ - value	$V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$	$I^2t$	425	$\text{A}^2\text{s}$

**Charakteristische Werte / Characteristic Values**

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 50 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 50 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_F$	1,80 1,90	2,20	V V
Rückstromspitze Peak reverse recovery current	$I_F = 50 \text{ A}, -di_F/dt = 1200 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 900 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$I_{RM}$	76,5 83,5		A A
Sperrverzögerungsladung Recovered charge	$I_F = 50 \text{ A}, -di_F/dt = 1200 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 900 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$Q_r$	14,5 24,5		$\mu\text{C}$ $\mu\text{C}$
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 50 \text{ A}, -di_F/dt = 1200 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 900 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{rec}$	7,60 13,5		mJ mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode		$R_{thJC}$		0,63	K/W
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	0,33		K/W
Temperatur im Schaltbetrieb Temperature under switching conditions			$T_{vj \text{ op}}$	-40	125	$^{\circ}\text{C}$

prepared by: RH	date of publication: 2013-10-03
approved by: RS	revision: 3.0



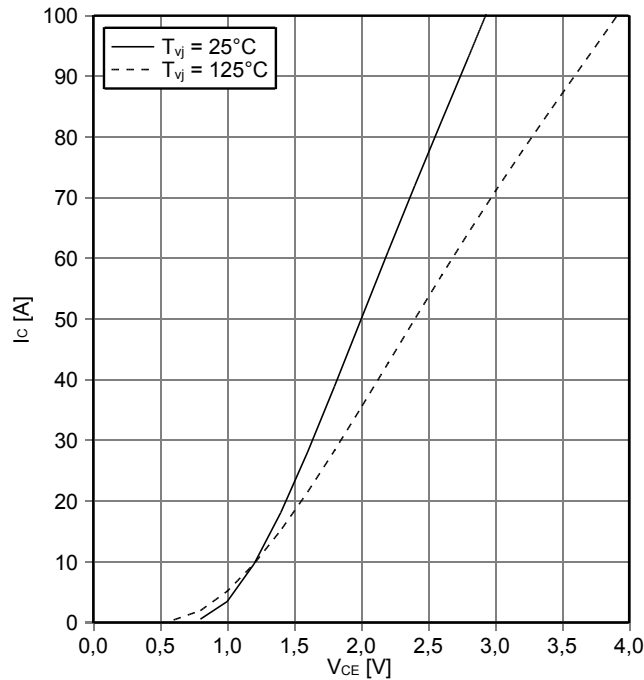
**Modul / Module**

Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V <sub>ISOL</sub>	3,4		kV
Material Modulgrundplatte Material of module baseplate			Cu		
Innere Isolation Internal isolation	Basisisolierung (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)		Al <sub>2</sub> O <sub>3</sub>		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		10,0 12,4		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		10,0 12,4		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI	> 200		
			min. typ. max.		
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R <sub>thCH</sub>	0,02		K/W
Modulstreuinduktivität Stray inductance module		L <sub>sCE</sub>	40		nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T <sub>c</sub> = 25°C, pro Schalter / per switch	R <sub>CC+EE'</sub>	2,50		mΩ
Lagertemperatur Storage temperature		T <sub>stg</sub>	-40	125	°C
Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting	Schraube M5 - Montage gem. gültiger Applikationsschrift Screw M5 - Mounting according to valid application note	M	3,00	-	6,00 Nm
Gewicht Weight		G	180		g

prepared by: RH	date of publication: 2013-10-03
approved by: RS	revision: 3.0

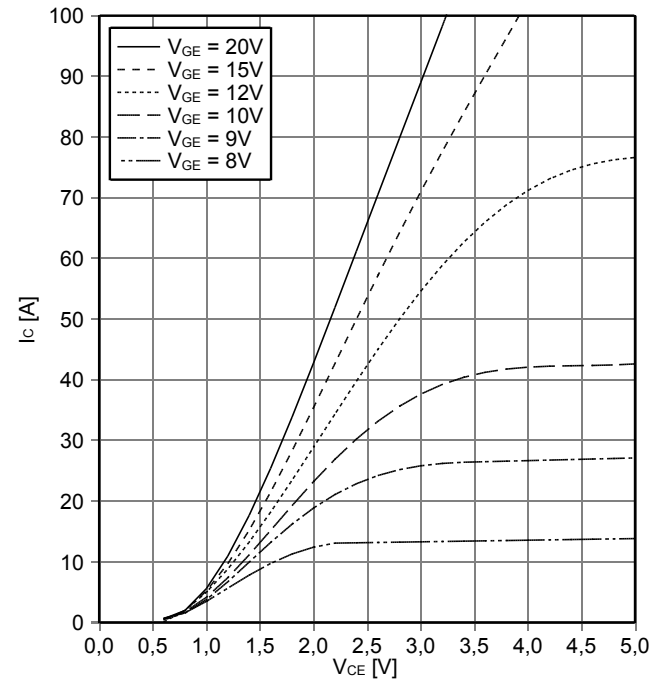
**Ausgangskennlinie IGBT, Wechselrichter (typisch)**  
**output characteristic IGBT, Inverter (typical)**

$I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



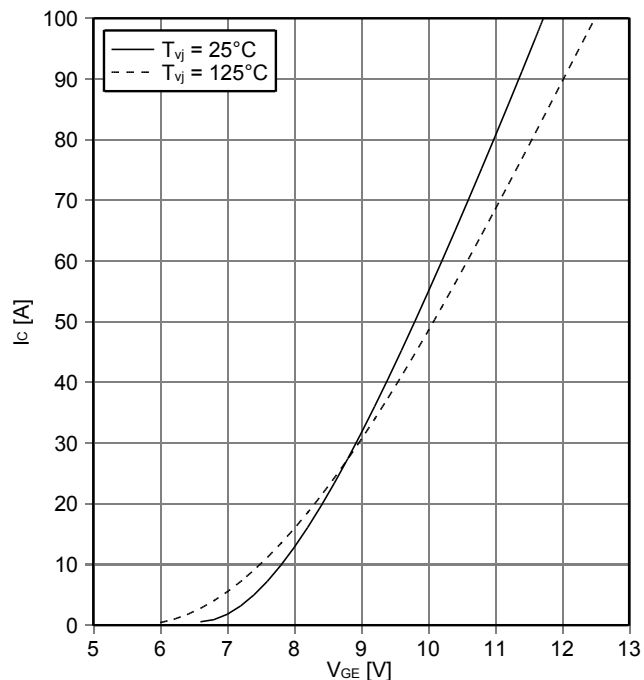
**Ausgangskennlinienfeld IGBT, Wechselrichter (typisch)**  
**output characteristic IGBT, Inverter (typical)**

$I_C = f(V_{CE})$   
 $T_{vj} = 125^\circ\text{C}$



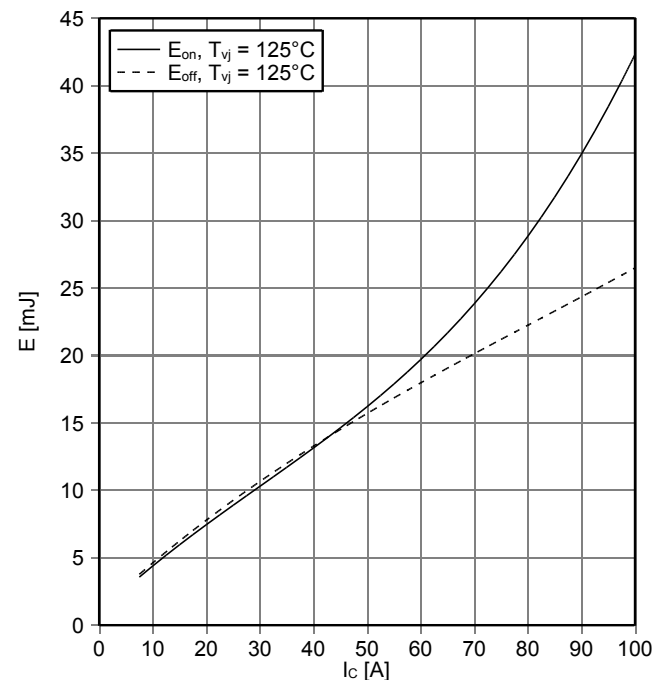
**Übertragungscharakteristik IGBT, Wechselrichter (typisch)**  
**transfer characteristic IGBT, Inverter (typical)**

$I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



**Schaltverluste IGBT, Wechselrichter (typisch)**  
**switching losses IGBT, Inverter (typical)**

$E_{on} = f(I_C), E_{off} = f(I_C)$   
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 8\ \Omega, R_{Goff} = 8\ \Omega, V_{CE} = 900\text{ V}$

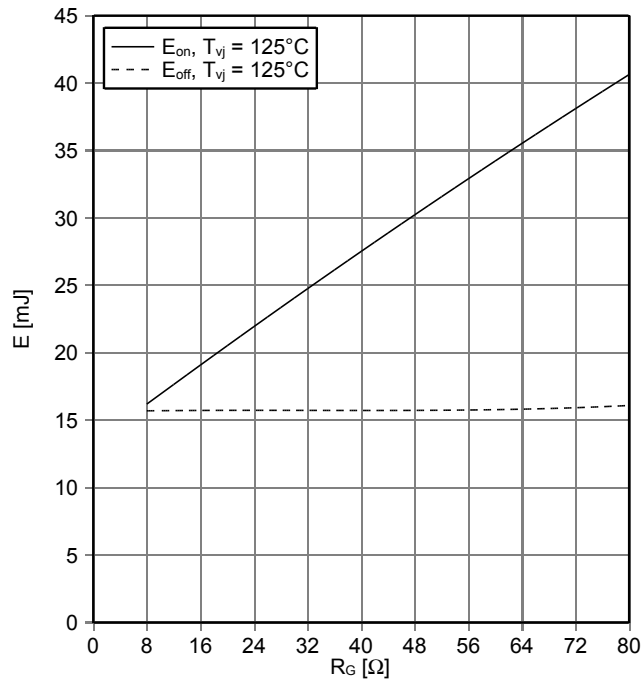


prepared by: RH	date of publication: 2013-10-03
approved by: RS	revision: 3.0



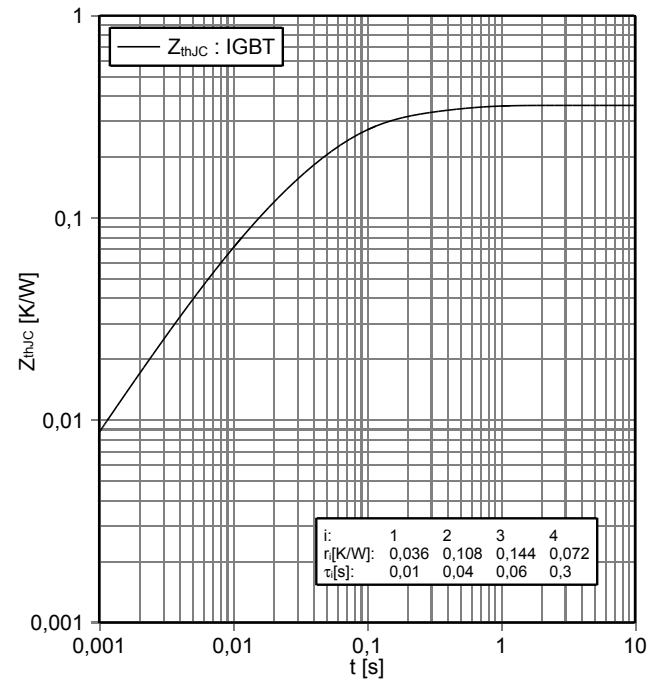
**Schaltverluste IGBT, Wechselrichter (typisch)**  
**switching losses IGBT, Inverter (typical)**

$E_{on} = f(R_G)$ ,  $E_{off} = f(R_G)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $I_C = 50\text{ A}$ ,  $V_{CE} = 900\text{ V}$



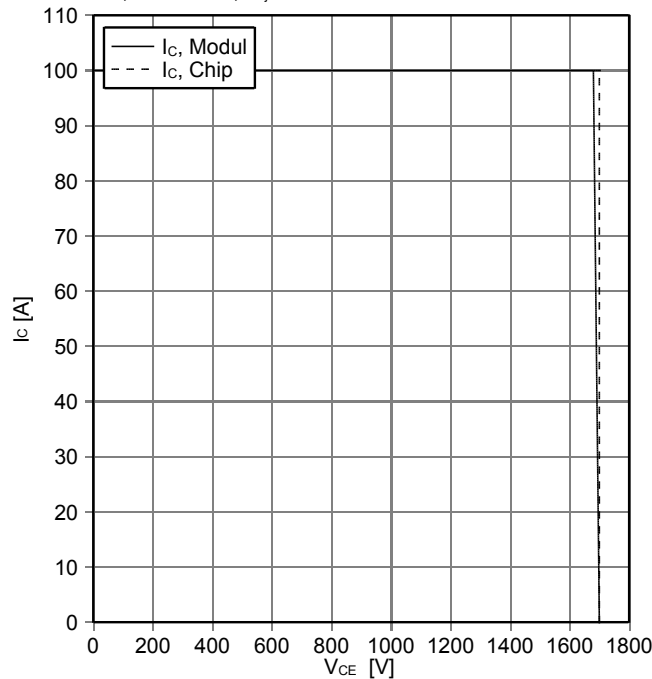
**Transienter Wärmewiderstand IGBT, Wechselrichter**  
**transient thermal impedance IGBT, Inverter**

$Z_{thJC} = f(t)$



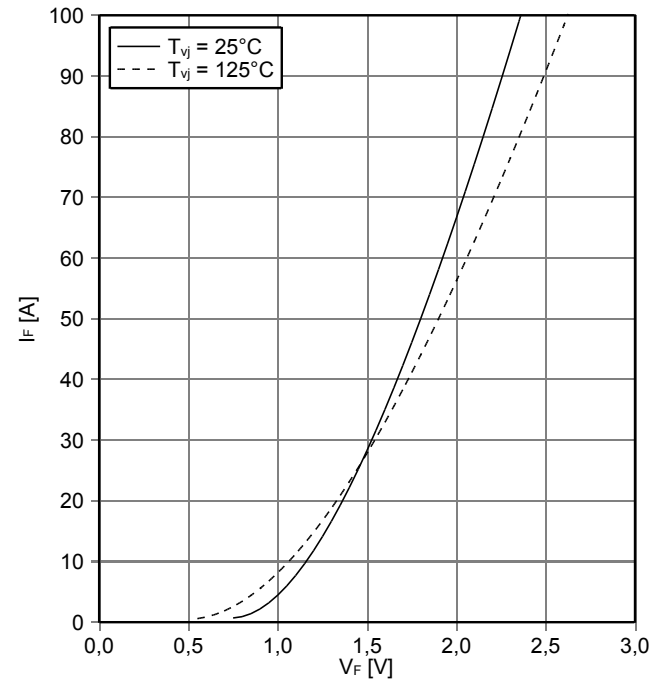
**Sicherer Rückwärts-Arbeitsbereich IGBT, Wechselrichter (RBSOA)**  
**reverse bias safe operating area IGBT, Inverter (RBSOA)**

$I_C = f(V_{CE})$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Goff} = 8\ \Omega$ ,  $T_{vj} = 125^\circ\text{C}$



**Durchlasskennlinie der Diode, Wechselrichter (typisch)**  
**forward characteristic of Diode, Inverter (typical)**

$I_F = f(V_F)$

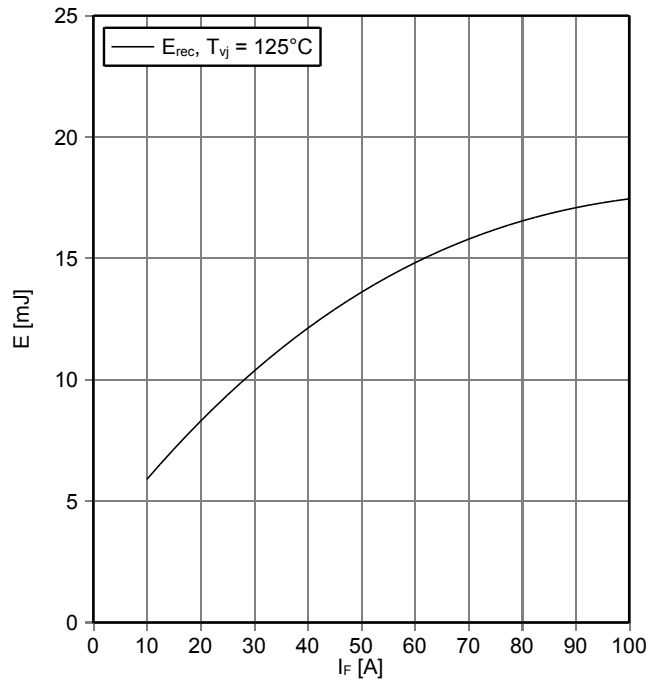


prepared by: RH	date of publication: 2013-10-03
approved by: RS	revision: 3.0



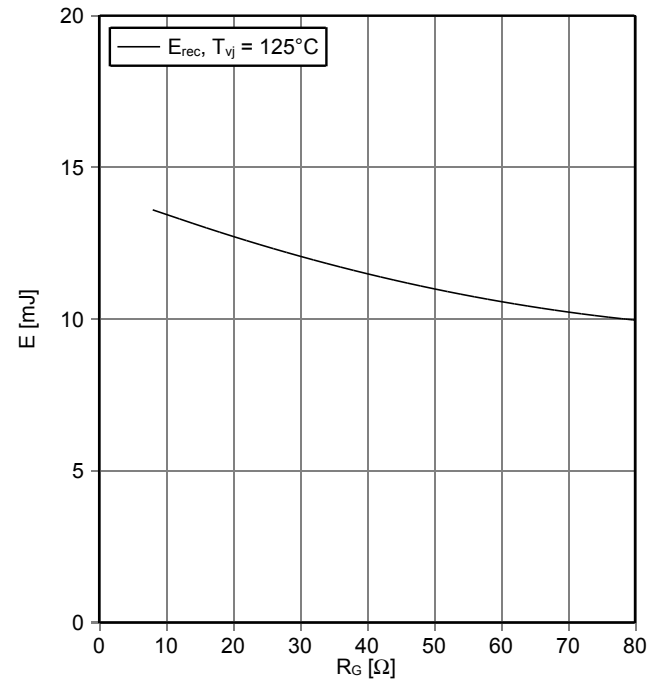
**Schaltverluste Diode, Wechselrichter (typisch)**  
**switching losses Diode, Inverter (typical)**

$E_{rec} = f(I_F)$   
 $R_{Gon} = 8 \Omega, V_{CE} = 900 V$



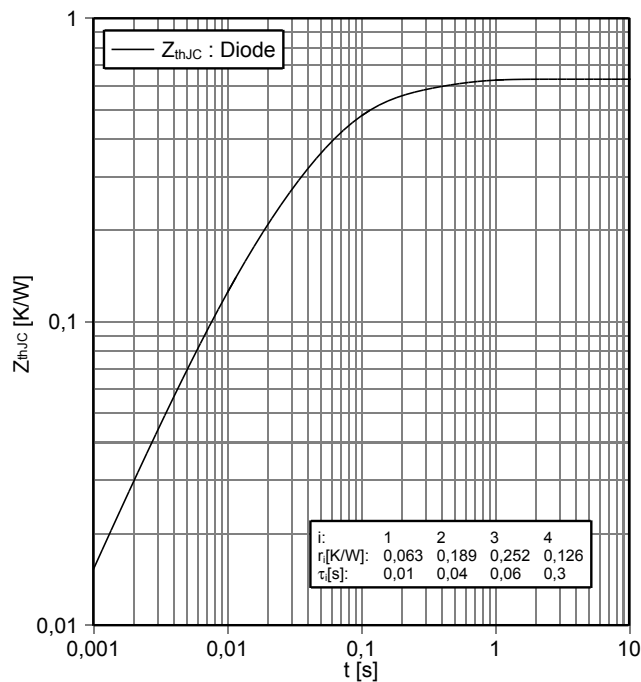
**Schaltverluste Diode, Wechselrichter (typisch)**  
**switching losses Diode, Inverter (typical)**

$E_{rec} = f(R_G)$   
 $I_F = 50 A, V_{CE} = 900 V$



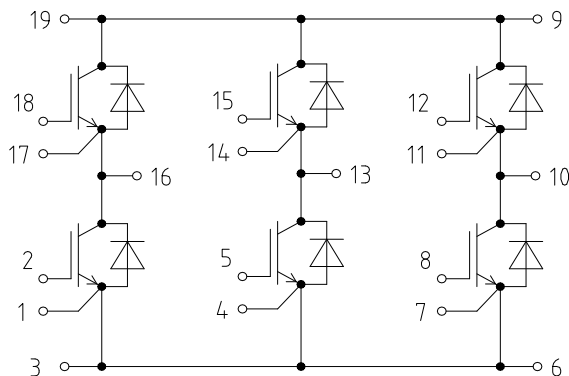
**Transienter Wärmewiderstand Diode, Wechselrichter**  
**transient thermal impedance Diode, Inverter**

$Z_{thJC} = f(t)$

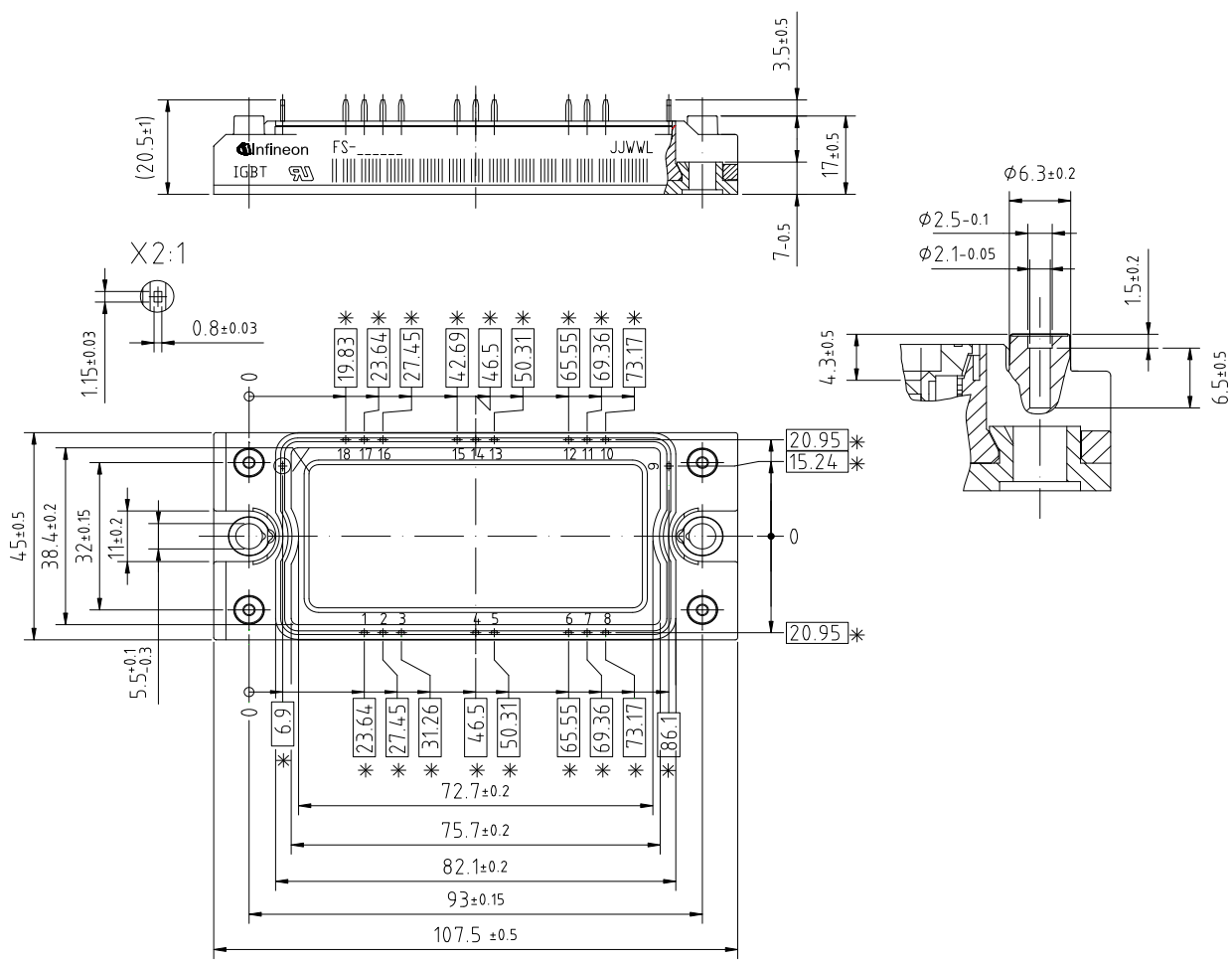


prepared by: RH	date of publication: 2013-10-03
approved by: RS	revision: 3.0

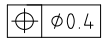
## Schaltplan / circuit\_diagram\_headline



## Gehäuseabmessungen / package outlines



\* = alle Maße mit einer Toleranz von  
\* = all dimensions with tolerance of



prepared by: RH	date of publication: 2013-10-03
approved by: RS	revision: 3.0